

SPEC SHEET (FOR REFERENCE)	SHEET No. G05007A	Rev. 4	Page. 1 of 1
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TYPE:6PT902N1T * *	
CHIP SIZE	0.55 * 0.55mm
WAFER SIZE	6 inch

Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-Source voltage	VDSS	20	V
Gate-Source voltage	VGSS	±8	V

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS1			±1	uA	VGS=±8V, VDS=0V
2	IGSS2			±0.2	uA	VGS=±4.5V, VDS=0V
3	IDSS			0.5	uA	VDS=20V, VGS=0V
4	BVDSS	22			V	ID=100uA, VGS=0V
5	Vth	0.53		1	V	ID=250uA, VGS=VDS
6	RDS(on)1		0.4	0.55	Ω	VGS=4.5V, ID=540mA
7	RDS(on)2		0.5	0.7	Ω	VGS=2.5V, ID=500mA
8	RDS(on)3		0.7	0.9	Ω	VGS=1.8V, ID=350mA
9	VSD	0.5		1.1	V	IS=115mA, VGS=0V
10	Yfs	200			mS	VDS=10V, ID=200mA

※Built in ZD between Gate and Source

PHENITEC SEMICONDUCTOR Corp.